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U.S. PATENT DOCUMENTS

Examiner Initial*		Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate
NN		6,291,861 B1	9/18/01	Iwata et al.			

FOREIGN PATENT DOCUMENTS

		Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No
NN		10-70195	3/10/98	Japan			No
NN		5-166837	7/2/93	Japan			No
NN		7-106574	4/21/95	Japan			No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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Examiner	NN ✓ NN	Date Considered	1-21-05

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